



www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3789, 2N3790, 2N3791, and 2N3792 are silicon PNP power transistors, manufactured by the epitaxial planar process, designed for medium speed switching and amplifier applications.

~~~~~~

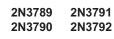
# MARKING: FULL PART NUMBER

|                                            |                                   | 2N3789        | 2N3790        |       |
|--------------------------------------------|-----------------------------------|---------------|---------------|-------|
| MAXIMUM RATINGS: (T <sub>C</sub> =25°C)    | SYMBOL                            | <u>2N3791</u> | <u>2N3792</u> | UNITS |
| Collector-Base Voltage                     | V <sub>CBO</sub>                  | 60            | 80            | V     |
| Collector-Emitter Voltage                  | V <sub>CEO</sub>                  | 60            | 80            | V     |
| Emitter-Base Voltage                       | V <sub>EBO</sub>                  | 7             | .0            | V     |
| Continuous Collector Current               | ۱ <sub>C</sub>                    | 1             | 0             | А     |
| Continuous Base Current                    | ۱ <sub>B</sub>                    | 4             | .0            | А     |
| Power Dissipation                          | PD                                | 15            | 50            | W     |
| Operating and Storage Junction Temperature | T <sub>J</sub> , T <sub>stg</sub> | -65 to        | +200          | °C    |
| Thermal Resistance                         | ΘJC                               | 1.            | 17            | °C/W  |

ELECTRICAL CHARACTERISTICS: (T<sub>C</sub>=25°C unless otherwise noted)

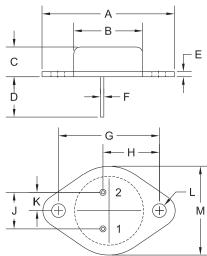
|                      |                                                                                        | 2N3789<br>2N3791 |     | 2N3790<br>2N3792  |     |       |  |
|----------------------|----------------------------------------------------------------------------------------|------------------|-----|-------------------|-----|-------|--|
| SYMBOL               | TEST CONDITIONS                                                                        | MIN              | MAX | <u>ZIN</u><br>MIN | MAX | UNITS |  |
| ICEV                 | V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>EB</sub> =1.5V                        | -                | 1.0 | -                 | 1.0 | mA    |  |
| ICEV                 | V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>EB</sub> =1.5V, T <sub>C</sub> =150°C | -                | 5.0 | -                 | 5.0 | mA    |  |
| I <sub>EBO</sub>     | V <sub>EB</sub> =7.0V                                                                  | -                | 5.0 | -                 | 5.0 | mA    |  |
| BVCEO                | I <sub>C</sub> =200mA                                                                  | 60               | -   | 80                | -   | V     |  |
| V <sub>CE(SAT)</sub> | I <sub>C</sub> =4.0A, I <sub>B</sub> =400mA (2N3789, 2N3790)                           | -                | 1.0 | -                 | 1.0 | V     |  |
| V <sub>CE(SAT)</sub> | I <sub>C</sub> =5.0A, I <sub>B</sub> =500mA (2N3791, 2N3792)                           | -                | 1.0 | -                 | 1.0 | V     |  |
| V <sub>BE(ON)</sub>  | V <sub>CE</sub> =2.0V, I <sub>C</sub> =5.0A (2N3789, 2N3790)                           | -                | 2.0 | -                 | 2.0 | V     |  |
| V <sub>BE(ON)</sub>  | V <sub>CE</sub> =2.0V, I <sub>C</sub> =5.0A (2N3791, 2N3792)                           | -                | 1.8 | -                 | 1.8 | V     |  |
| V <sub>BE(ON)</sub>  | V <sub>CE</sub> =4.0V, I <sub>C</sub> =10A                                             | -                | 4.0 | -                 | 4.0 | V     |  |
| hFE                  | V <sub>CE</sub> =2.0V, I <sub>C</sub> =1.0A (2N3789, 2N3790)                           | 25               | 90  | 25                | 90  |       |  |
| hFE                  | V <sub>CE</sub> =2.0V, I <sub>C</sub> =1.0A (2N3791, 2N3792)                           | 50               | 180 | 50                | 180 |       |  |
| h <sub>FE</sub>      | V <sub>CE</sub> =2.0V, I <sub>C</sub> =3.0A (2N3789, 2N3790)                           | 15               | -   | 15                | -   |       |  |
| h <sub>FE</sub>      | V <sub>CE</sub> =2.0V, I <sub>C</sub> =3.0A (2N3791, 2N3792)                           | 30               | -   | 30                | -   |       |  |
| fT                   | V <sub>CE</sub> =10V, I <sub>C</sub> =500mA, f=1.0MHz                                  | 4.0              | -   | 4.0               | -   | MHz   |  |
|                      |                                                                                        |                  |     |                   |     |       |  |

R2 (31-July 2013)





SILICON PNP POWER TRANSISTORS



#### DIMENSIONS INCHES MILLIMETERS MIN MAX MIN MAX SYMBOL 38.50 39.96 1.516 1.573 А B (DIA) 0.748 0.875 19.00 22.23 0.250 0.450 6.35 11.43 С 0.516 13.10 0.433 11.00 D Е 0.054 0.065 1.38 1.65 F 0.035 0.045 0.90 1.15 G 29.90 30.40 1.177 1.197 Н 0.650 0.681 16.50 17.30 0.420 0.440 10.67 11.18 J Κ 0.205 0.225 5.21 5.72 (DIA) 0.151 0.172 3.84 4.36 0.984 1.050 25.00 26.67 Μ TO-3 (REV: R2)

LEAD CODE:

| 1 | ) E | Bas | se |
|---|-----|-----|----|
|   |     |     |    |

2) Emitter Case) Collector

MARKING: FULL PART NUMBER



R2

**TO-3 CASE - MECHANICAL OUTLINE** 

www.centralsemi.com

R2 (31-July 2013)

# **OUTSTANDING SUPPORT AND SUPERIOR SERVICES**

#### **PRODUCT SUPPORT**

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- · Consolidated shipping options

### **DESIGNER SUPPORT/SERVICES**

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities

ss your design challenges.

· Custom product packing

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits

Custom bar coding for shipments

Custom product and package development

## **REQUESTING PRODUCT PLATING**

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

# CONTACT US

## **Corporate Headquarters & Customer Support Team**

Central Semiconductor Corp. 145 Adams Avenue Hauppauge, NY 11788 USA Main Tel: (631) 435-1110 Main Fax: (631) 435-1824 Support Team Fax: (631) 435-3388 www.centralsemi.com

Worldwide Field Representatives: www.centralsemi.com/wwreps

Worldwide Distributors: www.centralsemi.com/wwdistributors

For the latest version of Central Semiconductor's **LIMITATIONS AND DAMAGES DISCLAIMER**, which is part of Central's Standard Terms and Conditions of sale, visit: <u>www.centralsemi.com/terms</u>

